

REVIEW ARTICLE

Ceramic compositions for 5G devices containing niobium: A survey

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Abstract

The main dielectric properties of several ceramic materials having niobium in their composition, proposed to take part in 5G telecommunication devices, are reviewed. A preliminary basic presentation of 5G systems, the requirements for implementing their use, a concise review of the ceramic compositions containing niobium that have been studied thus far, and an evaluation of their performance are detailed. A survey is presented, including more than 80 different compositions containing niobium, focusing on key parameters, such as dielectric constant, quality factor, temperature coefficient, and sintering temperature. These parameters play a role for assessing the potential application of these ceramics in 5G devices.

KEYWORDS

5G, ceramics, dielectric properties, niobium compounds, wireless communication

1 | INTRODUCTION

Nowadays, wireless communication systems are continuously advancing, particularly for their application in mobile devices and satellite broadcasting, allowing access to previously inaccessible regions of the Earth and space satellite pathways. Ceramic materials play a vital role in this development, due to their favorable dielectric behavior, enabling their utilization in devices that require high-frequency response, such as resonators, antennas, and filters.¹⁻³ Furthermore, numerous ceramic compositions meet the essential requirements for their integration into communication system devices, including the availability of raw materials, straightforward synthesis techniques for obtaining suitable powders, low-temperature densification, and compatibility with metal electrodes during sintering, as well as mechanical reliability despite their small dimensions. The ongoing research focuses on

electroceramics with minimal signal latency (no delays between transmitted and received signals), suitable dielectric constants, and extremely low (near-zero) temperature coefficients. Although 5G telecommunication devices have already been partially implemented, research efforts are underway looking for low-cost ceramic materials with enhanced properties.

1.1 | Brief historical overview

Wireless communication originated with analogic devices for 1G systems in 1980. In 1991, 2G systems were introduced, utilizing digital signals and incorporating technologies, such as GPRS (*General Packet Radio Service*) and EDGE (*Enhanced Data Rates for GSM Evolution*), which enabled devices to connect via the internet. In 2001, 3G systems were launched, offering higher data transfer rates and

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exploiting dielectric materials with ultra-low loss tangent. The advent of 4G technology occurred in 2011, employing metalized dielectric ceramics as filters, allowing specific wave frequencies to be transmitted. Currently, there is a significant demand for communication devices operating in the 700 MHz–2.7 GHz range. Modern wireless communication requires even faster data transfers. 5G systems provide data transfer rate at least 10 times higher, low latency, and improved man-machine connectivity.^{1–3} The 5G chipset market was estimated at US\$ 490 million in 2018 and projected to reach US\$ 10.9 billion by 2024.⁴

For communication systems operating in the microwave frequency range, dielectric ceramics with specific characteristics are required. These characteristics include: (1) high dielectric constant ($20 \leq \epsilon_r \leq 35$) to allow for producing miniaturized devices; (2) high-quality factor ($Q_{xf} \geq 100\,000$ GHz), to improve signal quality and to allow for frequency tuning, allowing the use of multiple channels at different frequencies; (3) near-zero temperature coefficient (TCF or $\tau_f \sim 0 \pm 2$ ppm/°C) at the resonance frequency: the dielectric response should remain constant despite ambient temperature variations, such as the transition from winter to summer (-30°C to $+30^\circ\text{C}$), or the range of -55°C to $+85^\circ\text{C}$, depending on the satellite or space vehicle's position; and (4) sintering temperature lower than 950°C , to facilitate the deposition of silver electrodes and ensure chemical compatibility between the dielectric material and the electrodes.⁵

Many research reports in this field are primarily concerned with finding cost-effective materials and establishing correlations between microstructural characteristics and dielectric properties. Dielectric ceramics with various parameters find applications based on their specific characteristics: (1) high dielectric constant: these ceramics are advantageous as they can reduce signal transmission delays; (2) high-quality factors: these ceramics are beneficial in reducing power losses within the system; (3) near-zero temperature coefficients: these ceramics contribute to improved thermal stability of the system, ensuring minimal variation in dielectric constant under temperature changes; and (4) sintering temperature below 950°C : enables the application of these ceramics for the utilization of low-cost silver electrodes, providing cost-effective solutions. Exploring these parameters and their correlations with microstructural characteristics, researchers aim to identify and develop dielectric ceramics that meet specific requirements for various applications.^{6,7}

The operation frequencies of 5G communication systems are higher than those used in 4G systems. They include 3.5, 3.7, and 4.7 GHz frequencies, and the 26, 28, and 39 GHz millimeter waves (wavelength of the order of mm).^{1–3}

Data extracted from the Web of Science database using the keywords “5G” with “ceramics” and “5G” with “Nb”

show an exponential increase in the number of publications and citations starting from 2016 for both sets of keywords, indicating a growing interest and research activity in these areas.

1.2 | Ceramics for 5G

Ceramics used in 5G applications are typically polycrystalline inorganic compounds, either as sintered pellets or thin and thick films. Their primary function is to serve as dielectrics operating at frequencies in the GHz range. Significant research efforts have been dedicated to exploring the use of dielectric ceramics in 5G (and more recently for 6G) for communication devices.⁸ These are the dielectric properties that have to be evaluated: the dielectric constant, which determines the material's ability to store electrical energy; the quality factor, which reflects the material's efficiency in transmitting and storing energy; and the temperature coefficient, which indicates the material's sensitivity to temperature changes. Additionally, the sintering temperature is also important to ensure compatibility with the integration of electronic components through metal electrodes.^{8,9}

Defining those parameters:

- dielectric constant (ϵ_r): is the ratio of the dielectric capacitance to that of the vacuum. It expresses the ability of the dielectric to store energy when submitted to an electric voltage. That ability is usually ascribed to electric dipoles in the crystalline structure of the compound. One simple example of a dipole is the $\text{Y}^{3+}\text{-O}^{2-}\text{-Y}^{3+}$ complex in yttria-stabilized zirconia. Higher values mean the possibility of using ceramic pieces with small dimensions, decreasing the size of devices and also the cost/weight ratio. The dielectric constant is known to depend on the polarizability.^{10,11}
- the quality factor (Q_{xf}) of a dielectric material is defined as the product of the standing time and the resonance frequency. It represents the duration for which the resonance oscillation (wireless signal) of the dielectric remains active. A higher Q_{xf} indicates better frequency selectivity and a longer operation time at the desired frequency. The quality factor depends on both intrinsic and extrinsic losses. Intrinsic losses are associated with modes of lattice vibration within the material, while extrinsic losses are related to lattice defects, such as oxygen vacancies, porosity, and secondary phases. The quality factor is particularly significant in applications such as long-distance medical surgeries, where the instantaneous response of the surgeon is critical during the manipulation of surgical devices. A higher quality factor ensures improved frequency selectivity and

stability, contributing to enhanced performance and precision in such applications.

- the temperature coefficient (τ_f) is a measure of how the dielectric constant varies with temperature. A near-zero value indicates better thermal stability, making it more suitable for applications in devices that may be located at regions of varying temperature, for example, desert areas (northern Africa), polar regions (northern Hemisphere), or satellites.
- the sintering temperature (T_s) refers to the temperature required to obtain a dense ceramic compound, usually prepared by solid-state reaction among the constituents' oxides, to achieve a solid solution and/or densification. Lower values mean easiness to deposit low-cost metal electrodes, usually silver, which melts at 960°C. Lower sintering temperatures can help in reducing the energy consumption and cost associated with the sintering process. Operating at lower temperatures can save energy and make the manufacturing process more cost-effective.

It is widely acknowledged that the performance of ceramics in 5G devices is highly dependent on their microstructure. The dielectric constant ϵ_r depends on the relative density, due to the contribution of the porosity and of the unit cell volume that defines the polarizability. The quality factor Qxf depends on the binding energy of the (cation)-(oxygen ion) bond, as well as the average grain size. Microstructural features are considered due to the dependence of the dielectric properties on bulk density, porosity, average grain size, grain size distribution, and secondary phases.¹² Understanding and controlling these microstructural aspects are essential for optimizing the performance of these materials in 5G applications. Earlier studies on ceramic materials for 3G technology highlighted the relevance of the structure and microstructure on the dielectric properties. In the sequence, as an example, a brief review on complex perovskite ceramics for use in 5G telecommunication devices is given.

Ceramic materials with perovskite structure were fully investigated due to their excellent dielectric properties. The complex perovskite $\text{BaZn}_{1/3}\text{Ta}_{2/3}\text{O}_3$ is an example, with $\epsilon_r = 30$, Qxf = 150 000, and $\tau_f = 0$ ppm/°C. Substitution of Ta_2O_5 for Nb_2O_5 was promptly performed in these complex perovskites, to improve the cost effectiveness of the dielectric ceramics. Moreover, Ta_2O_5 -based complex perovskite ceramics usually require high sintering temperatures to achieve good densification. The $\text{BaZn}_{1/3}\text{Nb}_{2/3}\text{O}_3$ (BZN) ceramic exhibited $\epsilon_r = 38$, Qxf = 90 000, and $\tau_f = 30$ ppm/°C.¹³ Attempts have been made to decrease the value of τ_f changing the compositional variation. The composite $0.9[(\text{Zn}_{0.60}\text{Co}_{0.40})_{0.33}\text{Nb}_{0.67}]\text{O}_3-0.1\text{Ba}(\text{Ga}_{0.5}\text{Ta}_{0.5})\text{O}_3$, $0.9\text{BCZN}-0.1\text{BGT}$, for example, showed $\epsilon_r = 35$, $Q = 32$ 000, $f = 3.056$, and $\tau_f = 0$ ppm/°C.¹⁴

It was shown that the dielectric properties of complex perovskite structure such as $\text{AB}'_{1/3}\text{B}''_{2/3}\text{O}_3$ are strongly dependent on the cationic ordering, promoting a drastic decrease of the dielectric losses with increasing the degree of ordering. The 1:2 ordering of B-site cations is formed due to differences in size and valence of the two B-site ions. In this context, nonstoichiometry was also shown to play a role in the dielectric properties. The addition of up to 0.02 mol% $\text{Ba}_3\text{W}_2\text{O}_9$ to BZN increased the concentration of cation vacancies and decreased the sintering temperature due to liquid phase formation, resulting in highly dense ceramics. In addition, Zn vacancies were reported to accelerate the ordering process. These factors accounted for the high Qxf value (118 500) obtained at 8 GHz for $x = 0.007$.¹⁵ The relationship between ceramic processing and deviation from stoichiometry was also reported for $\text{BaCo}_{1/3}\text{Nb}_{2/3}\text{O}_3$ (BCN); although nonstoichiometry was barely detected, its influence was notorious on the extrinsic electrical conductivity.¹⁶ $\text{Ba}(\text{Mg}_{1/3-x}\text{Nb}_{2/3})\text{O}_3$ (BMN) compositions with $0 \leq x \leq 0.04$, prepared by the solid-state reaction method and sintered at 1450°C for 4 h, showed an increase of the cation ordering, and relative density for small Mg deficiency. The highest Q value achieved was 12 000 at 8 GHz for $x = 0.02$.¹⁷

It was clear from those previous studies that the processing and sintering profiles, besides partial substitutions, are important experimental procedures to tune the dielectric properties of ceramics.

Numerous ceramic compositions have been described as suitable for use in 5G devices: niobates, titanates, phosphates, silicates, molybdates, tantalates, and tungstates. In this survey, the focus is specifically on compositions containing niobium, and their main properties that are relevant for 5G devices. By narrowing down the investigation to niobium-containing compositions, the survey aims to highlight and analyze the main properties of these specific ceramics that are important for their application in 5G devices. Figure 1 shows a schematic view of the main issues focused on this survey.

This focused approach allows for a deeper understanding of the specific characteristics and performance requirements of niobium-based ceramic materials in the context of 5G technology.

2 | CERAMIC COMPOSITIONS FOR 5G DEVICES

Unless stated otherwise, all ceramic compounds here reviewed were synthesized by the solid-state reaction route or solid-state synthesis method. This involves the mixing of precursor oxides, followed by thermal treatment (calcination) in either resistive or microwave furnaces to achieve a solid solution. However, making direct

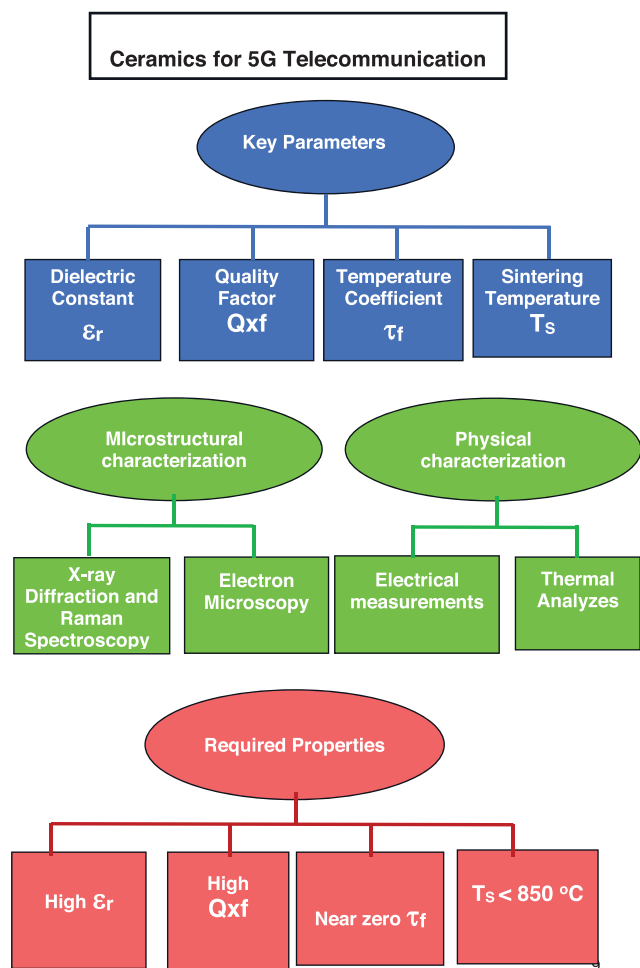


FIGURE 1 Scheme of the main topics addressed in this survey on ceramics for 5G telecommunication devices containing niobium: key parameters, microstructural and physical characterizations, and required properties (see text for details).

comparisons among the reported results can be challenging, primarily due to variations in experimental conditions during sample measurements. Moreover, the processing parameters varied, for example, the milling time, type and concentration of organic binders, calcination and sintering profiles, and other processing conditions, leading to different microstructures.

Nanosized powders are often synthesized using solution methods and are known to exhibit enhanced sinterability. However, these solution methods can be time-consuming and not cost-effective for large-scale technological applications. Then, the addition of both glass and nonglass sintering aids became common practice to reduce the sintering temperature required for the densification of ceramic compositions. The sintering aids usually facilitate the bonding between particles and enhance the mobility of atoms during the sintering process.

Initial studies on lithium niobates were conducted on cubic rock salt structures, including Li_3NbO_4 and $\text{Li}_3\text{Mg}_2\text{NbO}_6$. It was found that these ceramics exhibit the

dielectric constant in the range from 10 to 25; the Qxf value increased in the sequence Li_3NbO_4 and $\text{Li}_3\text{Mg}_2\text{NbO}_6$. Besides the relatively high Qxf values of compounds with rock salt structure, the τ_f value is not easily adjusted as for perovskite ceramics. In the latter, the τ_f may be tuned by changing the tilting angle of the corner-shared oxygen octahedrons. In rock salt structure ceramics, the edge-shared oxygen octahedrons are not expected to tilt in the same way. Good microwave dielectric properties were obtained for $\text{Li}_3\text{Mg}_2\text{NbO}_6$: $\epsilon_r = 16.8$, Qxf = 79 643 GHz, and $\tau_f = -27.2$ ppm/ $^\circ\text{C}$.¹⁸

A mixture of Li_3NbO_4 was co-fired with 20 wt.% Ag at 900°C , while pure Li_3NbO_4 was sintered in the 870 – 970°C range. The density of pure ceramic increased to $\sim 97\%$ as the sintering temperature reached a near steady-state at $\sim 930^\circ\text{C}$. The values of Qxf and ϵ_r also increased up to 930°C , whereas τ_f remained unchanged with the dwell temperature. The grain sizes observed in the ceramics were relatively small (1 – $2\ \mu\text{m}$), compared to other compositions. The optimal microwave dielectric properties were achieved for specimens sintered at 930°C , with $\epsilon_r = 15.8$, Qxf = 55 009 GHz at 8.99 GHz, and $\tau_f = -49$ ppm/ $^\circ\text{C}$.⁵

In the next two sections, $\text{Li}_3\text{Mg}_2\text{NbO}_6$ and other Li-based compositions will be described.

2.1 | $\text{Li}_3\text{Mg}_2\text{NbO}_6$ -based compositions

Reports on the synthesis of $\text{Li}_3\text{Mg}_2\text{NbO}_6$ date back to 1982.¹⁹ In recent years, the dielectric properties of lithium and magnesium niobates were consistently reported.^{20–22} Improvement of the dielectric properties was obtained with substitutional doping at Mg and Nb sites, for example, with Cu,¹⁰ Ta,¹¹ Co,²³ Ca,^{24,25} Ni,²⁵ Mn,²⁵ Sn,²⁶ Zn,^{25,27,28} Sb,²⁹ V,³⁰ Mo,³¹ W,³² Ti,^{33,34} co-doping with W-Li/Mg/Al/Ti,³⁵ co-doping with Li-Ti,³⁶ and using B_2O_3 ,³⁷ TiO_2 ,³⁸ $\text{MgO}+\text{B}_2\text{O}_3+\text{SiO}_2$,³⁹ and $\text{Li}_2\text{O}+\text{B}_2\text{O}_3+\text{SiO}_2+\text{CaO}+\text{Al}_2\text{O}_3$ ⁴⁰ sintering aids.

Early studies on $\text{Li}_3\text{Mg}_2\text{NbO}_6$ were conducted to verify the effects of partial substitutions of Mg^{2+} and Zn^{2+} into the Li^+ site of Li_3NbO_4 . Extensive solid solutions were expected to occur, due to the similarity in ionic radii between Li^+ , Mg^{2+} , and Nb^{5+} , as well as the similarity between the crystalline structure of Li_3NbO_4 and MgO . The specimens were sintered in the 1200 – 1350°C range. The crystal structure of $\text{Li}_{3-3x}\text{M}_{4x}\text{Nb}_{1-x}\text{O}_4$ ($0 < x \leq 0.9$), with $\text{M} = \text{Mg}, \text{Zn}$, was characterized by X-ray diffraction and Raman spectroscopy. For $x = 0$, the X-ray diffraction pattern of Li_3NbO_4 exhibited a cubic ordered structure along with a secondary phase, $\text{Nb}_{12}\text{O}_{29}$, which is characteristic of Nb reduction. The presence of this phase was attributed to the loss of Li by evaporation during the thermal treatment at high temperatures.⁴¹ The addition of Mg ($0.01 \leq x \leq 1/3$) promoted the stabilization of a disordered

cubic structure without the formation of secondary phases. On the other hand, the addition of Zn did not result in solid solution formation or the creation of a new compound. The X-ray diffraction patterns showed the presence of Li_3NbO_4 and ZnO throughout the entire composition range. The dielectric constant (ϵ_r) values for the studied compositions were in the 16.3–16.8 range. The quality factor varied from 32 765 ($x = 0$, sintered at $1150^\circ\text{C}/2$ h) to 85 160 GHz ($x = 0.2$, sintered at $1300^\circ\text{C}/2$ h), and the temperature coefficient (τ_f) from -22 ($x = 1/3$, sintered at $1300^\circ\text{C}/2$ h) to -45 ppm/ $^\circ\text{C}$ ($x = 0$, sintered $1150^\circ\text{C}/2$ h).⁴¹

2.2 | Pure $\text{Li}_3\text{Mg}_2\text{NbO}_6$

These ceramics, considered to be a promising candidate for devices operating in the millimeter wavelength spectral region, were prepared either pure,^{8,19} or with the addition of dopants or sintering aids^{10,11,23–40} for improving their properties or decreasing the sintering temperature. The dielectric properties of the pure compound sintered at 1250°C were $\epsilon_r = 16.8$, Qxf = 79 643 GHz, and $\tau_f = -27.2$ ppm/ $^\circ\text{C}$.³⁵ Stoichiometric $\text{Li}_3\text{Mg}_2\text{NbO}_6$ with submicron particle size (~ 222 nm) was obtained by high-energy milling. High relative density ($\sim 96\%$), $\epsilon_r \sim 18$, Qxf ~ 51 870 GHz, and $\tau_f \sim -23$ ppm/ $^\circ\text{C}$ were obtained for specimens sintered at 950°C ,²² evidencing the beneficial effect of the synthesis by chemical methods on densification.

$\text{Li}_{3+x}\text{Mg}_2\text{NbO}_6$ ($x = 0-0.08$): excess Li in the base composition allowed for a small decrease in the sintering dwell temperature (~ 1250 to $\sim 1150^\circ\text{C}$), and significant increase in the quality factor (~ 79 000 to ~ 150 000). The lattice parameter and cell volume increased, indicating that Li was incorporated into the crystal lattice. The bulk density and the dielectric constant were higher than those of the stoichiometric composition. The grain size increased up to $x = 0.04$ in the $\text{Li}_{3+x}\text{Mg}_2\text{NbO}_6$. The optimized parameters, assumed to be due to Li compensation owing to lithium volatilization during sintering, were $\epsilon_r \sim 16$, Qxf ~ 150 000 GHz, and $\tau_f \sim -29$ ppm/ $^\circ\text{C}$ ($x = 0.04$).²⁰

2.2.1 | $\text{Li}_3\text{Mg}_{2-x}\text{A}_x\text{NbO}_6$ partial substitution for the Mg^{2+} ion

In general, ceramics containing partial substitutions in the Mg^{2+} site exhibited dielectric constant values in the 14–16 range. However, the quality factor and temperature coefficient varied considerably, influenced by factors such as sintering temperature, density, and other variables.

Co-doping: $\text{Li}_3(\text{Mg}_{1-x}\text{Co}_x)_2\text{NbO}_6$ ($0.00 \leq x \leq 0.10$)

The Qxf values of samples sintered at $1300^\circ\text{C}/4$ h increased from 91 600 GHz for $x = 0$ to 127 600 GHz for $x = 0.02$.

No secondary phases were detected, and all compositions exhibited orthorhombic structure. The microwave dielectric properties were $\epsilon_r = 15.22$, Qxf = 127 600 GHz, and $\tau_f = -3.64$ ppm/ $^\circ\text{C}$.²³

Ca-doping: $\text{Li}_3(\text{Mg}_{1-x}\text{Ca}_x)_2\text{NbO}_6$ ($0.02 \leq x \leq 0.08$)

Ceramics were found in single phase with orthorhombic structure after sintering at $1060-1220^\circ\text{C}/6$ h. A more homogeneous microstructure with grain sizes in the 20–35 μm range was obtained after sintering at $1140^\circ\text{C}/6$ h, for $x = 0.04$, with $\epsilon_r \sim 16.81$, Qxf ~ 98 000 GHz, and $\tau_f \sim -25.8$ ppm/ $^\circ\text{C}$.²⁴ Based on experimental data, it was concluded that ϵ_r and Qxf are mainly related to density. LiF was used as a sintering aid to reduce the dwell temperature. The optimal microwave dielectric properties, $\epsilon_r = 15.85$, Qxf = 98 012 GHz, and $\tau_f = -28.6$ ppm/ $^\circ\text{C}$, were obtained after sintering at $900^\circ\text{C}/6$ h with 6 wt.% LiF.²⁴ Another work, doping with 0.05 mol Ca^{2+} , yielded $\epsilon_r = 15.62$, Qxf = 96 160 GHz (at 8.971 GHz), and $\tau_f = -18.49$ ppm/ $^\circ\text{C}$. The Qxf and ϵ_r values were comparatively lower for Mn^{2+} substitution in the Mg^{2+} site (52 700 GHz and 12.97, respectively) with $\tau_f = -20.13$ ppm/ $^\circ\text{C}$.²⁵ All the prepared compositions had rock salt structure.

Cu-doping: $\text{Li}_3\text{Mg}_{2-x}\text{Cu}_x\text{NbO}_6$ ($x = 0-0.04$)

These ceramics were shown to achieve high relative density after sintering at $1000-1120^\circ\text{C}$, with high value of ϵ_r (15.75), Qxf = 92 134 GHz (9.86 GHz), and near-zero $\tau_f = -2$ ppm/ $^\circ\text{C}$ for $x = 0.02$.¹⁰ In this case, ϵ_r was shown to correlate with the polarizability, whereas Qxf was influenced by the packing fraction.

Sn-doping: $\text{Li}_3\text{Mg}_{2-x/3}\text{Sn}_x\text{Nb}_{1-2x/3}\text{O}_6$

Simultaneous partial substitution on Mg^{2+} and Nb^{5+} sites were also investigated with Sn^{4+} doping in $\text{Li}_3\text{Mg}_{2-x/3}\text{Sn}_x\text{Nb}_{1-2x/3}\text{O}_6$ ($0 \leq x \leq 1.5$).²⁶ For x value up to 0.1, the compositions exhibited the typical orthorhombic structure of $\text{Li}_3\text{Mg}_2\text{NbO}_6$, which changed to the characteristic cubic phase of $\text{Li}_2\text{Mg}_3\text{SnO}_6$ for $x \geq 0.7$. The optimal dielectric parameters were found in a mixed orthorhombic-cubic ($x = 0.3$) phase field for specimens sintered at 1290°C with $\epsilon_r = 15.9$, Qxf = 118 700 GHz ($f = 7.99$ GHz), and $\tau_f = -32.9$ ppm/ $^\circ\text{C}$. Nevertheless, the temperature stable properties were obtained for $x = 1.2$ ($\epsilon_r = 11.64$, Qxf = 83 100 GHz at $f = 10.30$ GHz, and $\tau_f = 3.9$ ppm/ $^\circ\text{C}$).²⁶

Zn-doping: $\text{Li}_3(\text{Mg}_{1-x}\text{Zn}_x)_2\text{NbO}_6$ ($0 < x < 0.1$)

These ceramics exhibited the following microwave dielectric properties: $\epsilon_r = 17.2$, Qxf = 142 331 GHz, $\tau_f = 23.2$ ppm/ $^\circ\text{C}$ for $x = 0.08$ and sintered at $1120^\circ\text{C}/4$ h. Addition of a small amount of sintering aid, 0.5 wt.% ($0.17\text{Li}_2\text{O}-0.83\text{V}_2\text{O}_5$), allowed for sintering at $925^\circ\text{C}/2$ h

with the following microwave dielectric properties: $\epsilon_r = 14$, $Qxf = 83\,395$ GHz, and $\tau_f = 37.2$ ppm/°C.²⁷ X-ray diffraction evidenced that $Li_3Mg_2NbO_6$ was the main crystalline phase, besides minor amounts of secondary phases such as NbO and $Mg_4Nb_2O_9$, after sintering at 1200°C. Optimal dielectric properties were obtained for $x = 0.04$ with $\epsilon_r = 16.3$, $Qxf = 93\,100$ GHz, and $\tau_f = -34.1$ ppm/°C. Adding Li^+ and Zn^{2+} , the composition $Li_{3.04}Mg_{1.96}Zn_{0.04}Nb_{0.96}Ti_{0.04}O_6$ yielded $\epsilon_r = 16.3$, $Qxf = 93\,100$ GHz, and $\tau_f = -34.1$ ppm/°C.²⁸

Li₃(Mg_{0.95}A_{0.05})₂NbO₆ (A = Ca²⁺, Ni²⁺, Zn²⁺, Mn²⁺)

These ceramic compositions were sintered at 1120–1240°C/4 h in air. X-ray diffraction evidenced solid solution formation with rock salt structure; the following parameters were obtained: A = Ca²⁺, $\epsilon_r = 15.62$, $Qxf = 96\,160$ GHz, and $\tau_f = -18.47$ ppm/°C; A = Ni²⁺, $\epsilon_r = 15.24$, $Qxf = 84\,810$ GHz, and $\tau_f = -23.08$ ppm/°C; A = Zn²⁺, $\epsilon_r = 15.39$, $Qxf = 82\,170$ GHz, and $\tau_f = -18.57$ ppm/°C; A = Mn²⁺, $\epsilon_r = 12.97$, $Qxf = 52\,700$ GHz, and $\tau_f = -20.13$ ppm/°C.²⁵ In this case, Qxf and τ_f varied similarly to the packing fraction and to the Mg site bond valence, respectively. These results show that Ca²⁺ and Zn²⁺ exert almost the same effect on the dielectric properties.

2.2.2 | $Li_3Mg_2Nb_{1-x}A_xO_6$ partial substitution for the Nb⁵⁺ ion

Regarding partial substitutions in the Nb⁵⁺ site with both isovalent and aliovalent cations, interesting characteristics were observed. In particular, the dielectric constant remained similar (~16) with the substitution of Nb⁵⁺ for M⁵⁺ cations (M⁵⁺ = V, Sb, and Ta). The addition of Ta promoted grain growth and increase of the density, contributing to decrease the fraction of grain boundaries and, consequently, to reduce the dielectric loss. However, a significant increase of the Qxf value was observed for V⁵⁺ (~131 000 GHz) and near-zero τ_f for Ta⁵⁺ (−4.5 ppm/°C) substitutions. The sintering temperature was relatively lower for V⁵⁺ addition (900°C) and higher for Ta⁵⁺ addition (1150°C).^{11,30}

Sb-doping: $Li_3Mg_2(Nb_{1-x}Sb_x)O_6$ (0.02 ≤ x ≤ 0.08)

Ceramic compositions were prepared by calcination of stoichiometric amounts of lithium carbonate and magnesium, niobium, and antimony oxides, pressing into pellets and sintering at 1075–1200°C/6 h. Substitution of Sb⁵⁺ in the Nb⁵⁺ site provided a large increase of the quality factor and grain growth. The $Li_3Mg_2(Nb_{0.94}Sb_{0.06})$ sintered at 1150°C/6 h showed 15.79, 94 487 GHz, and −24.53 ppm/°C for the dielectric constant ϵ_r , the quality factor Qxf , and the temperature coefficient τ_f , respectively.²⁹

V-doping: $Li_3Mg_2Nb_{1-x}V_xO_6$ (x = 0.02, 0.04, 0.06, 0.08)

$Li_3Mg_2NbO_6$ was mixed to vanadium oxide (xV_2O_5 , 0.25 ≤ x ≤ 1.25 wt.%) to reduce the sintering temperature. Specimens sintered at 925°C/4 h exhibited a dense microstructure with grain sizes in the ~8 to ~11 μm range. The ideal concentration of V₂O₅ was 1 wt.%, with $\epsilon_r \sim 15.1$, $Qxf = 91\,000$ GHz, and $\tau_f \sim -24$ ppm/°C.²¹ The Qxf value was influenced by the relative density and the average grain size.

Ta-doping: $Li_3Mg_2Nb_{1-x}Ta_xO_6$

Ceramics with substitution in the Nb⁵⁺ site for Ta⁵⁺, and its effect on the structural characteristics and microwave dielectric performances was investigated. The composition sintered at 1100°C and with x = 0.02 displayed the microwave dielectric properties: $\epsilon_r = 15.58$, $Qxf = 113\,000$ GHz, and $\tau_f = -4.5$ ppm/°C. Specimens containing partial substitution in the Nb⁵⁺ site for Ta⁵⁺ exhibited a high-quality factor for x = 0.03, with an average grain size of ~10 μm.¹¹ The temperature coefficient τ_f was shown to be impacted by the NbO₆ octahedral distortion and Nb-O bond valence.

Mo-doping: $Li_3Mg_2(Nb_{(1-x)}Mo_x)O_{6+x/2}$ (0 ≤ x ≤ 0.08)

Substitution of Mo⁶⁺ in the Nb⁵⁺ site modified the grain size from 50–90 (x = 0) to 10–20 μm (x = 0.8) after sintering at 1200°C. The quality factor increased, with maximum value at x = 0.02 (116 266 GHz), and then decreased, whereas τ_f increased with increasing Mo content from ~−20 to ~−16 ppm/°C.³¹ The ionic radius of Mo⁶⁺ is smaller than that of Nb⁵⁺ and a shift of the diffraction peaks toward higher angles was observed. As in other dielectric ceramics, the Qxf value was closely related to specimen density and bond valence.

W-doping: $Li_3Mg_2Nb_{1-x}W_xO_{6+x/2}$

The introduction of W⁶⁺ in the Nb⁵⁺ site promoted grain growth and increase of the density achieving > 96% for x = 0.06, after sintering at 1175°C.³² In the case of substitution of M⁶⁺ (M⁶⁺ = Mo, W) for Nb⁵⁺, the dielectric properties were similar for sintering at 1200°C³¹ and 1175°C³² with ϵ_r 15–16, Qxf in the 116 266–124 187 GHz range, and τ_f of −15.82 to −18.28 ppm/°C. The quality factor was found to be influenced by the average bond valence and the density.

Ti-doping: $Li_{3+x}Mg_{2-2x}Nb_{1-x}Ti_{2x}O_6$ (0 ≤ x ≤ 1)

Several reports may be found concerning Ti-doping. Substitution of Ti⁴⁺ in the Nb⁵⁺ site, $Li_3Mg_{2-x/3}Nb_{1-2x/3}Ti_xO_6$ (0 ≤ x ≤ 0.6), was investigated from a structure point of view. A disordered cubic structure without secondary phases was obtained in the 0.12 ≤ x ≤ 0.38. The Qxf value increased

(82 338–125 357 GHz) with increasing x from 0 to 0.4, after sintering at 1260°C, with $\epsilon_r \sim 15$ and $\tau_f = -31.7$ ppm/°C.⁴² The main effect of partial substitution of Ti^{4+} in the Nb^{5+} site was to increase considerably the quality factor. A full range of solid solutions were found between $Li_3Mg_2NbO_6$ and Li_2TiO_3 with no trace of impurities.³⁴ The multicomponent $Li_{3+x}Mg_{2-2x}Nb_{1-x}Ti_xO_6$ exhibited high Qxf value (128 600 GHz) at $x = 0.2$ after sintering at 1250°C, with $\epsilon_r \sim 16$ and $\tau_f \sim -30.4$ ppm/°C. Temperature stable properties were found for $x = 0.9$ with $\epsilon_r = 20.4$, Qxf = 90 300 GHz ($f = 7.9$ GHz), and $\tau_f = 2.9$ ppm/°C.³⁴ In another study, the effect of Ti^{4+} with ionic radius (0.605 Å) similar to that of Nb^{5+} (0.64 Å) was studied for x up to 0.10 in $Li_3Mg_2Nb_{1-x}Ti_xO_{6-x/2}$, after sintering at 1150°C. The grain sizes obtained were comparatively small (typically ~ 10 μm), with $\epsilon_r \sim 15.9$, Qxf = 131 000 GHz, and $\tau_f = -26.8$ ppm/°C.³³

Efforts to enhance the properties of dielectric ceramics have been undertaken also through the strategy of co-doping.^{35,36}

Co-doping with W and Li/Mg/Al/Ti

The studied compositions, sintered at 1150°C/4 h, yielded the following values for ϵ_r , Qxf, and τ_f : $Li_3Mg_2Nb_{0.96}(Li_{1/5}W_{4/5})_{0.04}O_6$: 13.9806, 114 781, -22.33 ; $Li_3Mg_2Nb_{0.96}(Mg_{1/4}W_{3/4})_{0.04}O_6$: 13.8022, 105 879, -21.19 ; $Li_3Mg_2Nb_{0.96}(Al_{1/3}W_{2/3})_{0.04}O_6$: 13.7253, 102 760, -23.11 ; $Li_3Mg_2Nb_{0.96}(Ti_{1/2}W_{1/2})_{0.04}O_6$: 14.2356, 128 838, -21.12 ³⁵; $Li_3Mg_2Nb_{0.96}W_{0.04}O_6$: 16.8, 79 643, 27.2. No secondary phases were observed by X-ray diffraction, but a shift toward a higher angle in the diffraction peaks. Partial substitutions of W^{6+} in the Nb^{5+} site and Li^+ , Mg^{2+} , Al^{3+} , and Ti^{4+} in the complex $Li_3Mg_2Nb_{0.96}(M_xW_{1-x})_{0.04}O_6$ composition revealed single-phase ceramics up to $x = 0.04$. The Qxf value was higher for sintering temperatures of 1150°C/4 h with relative densities $\sim 96\%$. The highest value of Qxf (128 838 GHz) was obtained for $M = Ti^{4+}$. The τ_f values varied from -21.12 to -27.2 ppm/°C.³⁵ The quality factor increased linearly with increasing the average bond valence.

Co-doping with (Li^+/Ti^{4+})

$Li_{3.06}Mg_2Nb_{0.94}Ti_{0.06}O_6$ ceramics sintered at 1025°C/4 h, prepared with excess Li along with partial substitution of Ti^{4+} in the Nb^{5+} site resulted in suitable values of the dielectric constant (~ 14), quality factor (154 113 GHz), and τ_f (~ -2 ppm/°C), after sintering at 1025°C.³⁶ These results are further evidence that excess Li is beneficial to increase the quality factor. Moreover, the co-doping with Ti in the Nb site was very effective to achieve a near-zero τ_f , which varied in a similar way as the bond energy.

2.2.3 | With sintering aids

To reduce the sintering temperature, several reports have focused on the use of sintering aids. Boron oxide (B_2O_3) and boron-based glasses have been employed for this purpose.^{37–40} A complex glass based on Li_2O - B_2O_3 - SiO_2 - CaO - Al_2O_3 (LBSCA) was also incorporated to $Li_3Mg_2NbO_6$.⁴⁰

B_2O_3 adding: $Li_3Mg_2NbO_6 + x$ wt.% B_2O_3

Compounds, prepared by the solid-state method, had the sintering temperature reduced to 925°C/4 h. The dielectric constant and the quality factor varied according to the bulk density. Boron oxide added in small amounts ($x = 0.05$ – 1.5 wt.%) allowed for achieving 92% relative density after sintering at 950°C and promoted grain growth. Nevertheless, a secondary phase was detected by X-ray diffraction and observed on scanning electron microscopy micrographs. The quality factor value was shown to be influenced by the amount of the sintering aid and sintering temperature and τ_f varied from ~ -16 to ~ -22.5 ppm/°C with increasing amounts of B_2O_3 . The microwave dielectric properties $\epsilon_r = 14.0$, Qxf = 67 451 GHz, $\tau_f = -16.82$ ppm/°C were obtained for $Li_3Mg_2NbO_6$ – 0.1 wt.% B_2O_3 ceramics sintered at 925°C/4 h.³⁷

LBBS adding: $Li_3Mg_2NbO_6$ - $0.1TiO_2$

These ceramics were synthesized with the addition of Li_2O - B_2O_3 - Bi_2O_3 - SiO_2 glass. The glass addition allowed for reducing the sintering temperature of $Li_3Mg_2NbO_6$ - $0.1TiO_2$ to 900°C. A secondary phase (MgO) was detected by X-ray diffraction technique and τ_f shifted toward negative values. In this case, the dielectric constant ($\epsilon_r = 16$) did not change significantly, the Qxf value was 42 648 GHz, and a near-zero $\tau_f \sim -1$ ppm/°C was obtained.³⁸

MBS adding: $Li_3Mg_2NbO_6$

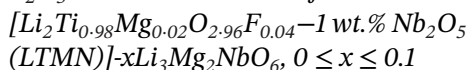
(0.1 – 2.0 wt.% MBS: 42 MgO, 45 B_2O_3 , 13 SiO_2) was obtained by calcination at 1050°C/4 h of stoichiometric amounts of lithium carbonate and magnesium and niobium oxides. Pellets obtained with an addition of 0.5 wt.% MBS glass were sintered at 925°C/4 h achieving 95% of relative density. The microwave dielectric properties were $\epsilon_r = 14.5$, Qxf = 80 759 GHz, and $\tau_f = -20.7$ ppm/°C.³⁹

LBSCA adding: $Li_3Mg_2NbO_6$

Ceramics with an addition of LBSCA glass were prepared with 52.45 Li_2O :31.06 B_2O_3 :11.99 SiO_2 :2.25 CaO :2.25 Al_2O_3 at 1000°C/4 h. The dielectric ceramic with 0.5 wt.% of the glass additive sintered at 925°C/4 h and showed $\epsilon_r = 15.16$, Qxf = 90 557 GHz, and $\tau_f = -16.22$ ppm/°C. The sintered density reached a maximum value ($\sim 96\%$ for 0.25 wt.%

LBSCA) for a sintering dwell temperature of 950°C. No secondary phases were detected by X-ray diffraction after sintering at 925°C. Increase of the sintering temperature to 975°C resulted in abnormal grain growth in specimens containing 0.5 wt.% of LBSCA.⁴⁰

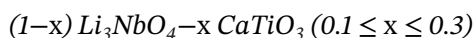
B₂O₃-CuO with addition of



Ceramics were prepared by solid-state synthesis and the sintering temperature was lowered from 1120°C to 750°C by adjusting the mass ratio of B₂O₃-CuO (BC), with a relatively low eutectic point. The dielectric properties ($\epsilon_r \sim 24.44$, Qxf ~ 60 574 GHz, and $\tau_f \sim 22.8$ ppm/°C) were obtained in BC-modified LTMN ceramics sintered at 790°C.⁴³

In general, sintering additives were found to be effective to reduce the sintering temperature, without compromising the dielectric properties of the ceramics.

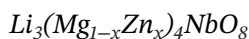
2.2.4 | Other compositions containing lithium



The composites were prepared, and the dielectric properties of lithium niobate changed according to calcium titanate additions. X-ray diffraction showed the Li₃NbO₄ cubic structure and CaTiO₃ perovskite structure. High density and high ϵ_r values were achieved after sintering at 1250°C. The temperature coefficient of resonant frequency could be adjusted to near-zero. Particularly, for $x = 0.15$, the ceramic sintered at 1025°C/4 h exhibited $\epsilon_r = 21.9$, Qxf = 24 900 GHz, and $\tau_f = 5.6$ ppm/°C.⁴⁴

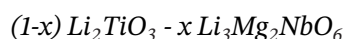
Li₃MgNbO₅

The composition with rock salt structure was synthesized by the two-step sintering method. The phase purity of Li₃MgNbO₅ was validated by X-ray diffraction in specimens sintered in the 1200–1280°C. The grain size increased from ~ 11 to ~ 40 μm according to the sintering temperature. Optimal properties ($\epsilon_r = 16.2$, Qxf = 96 796 GHz, and $\tau_f = -24.8$ ppm/°C) were obtained for sintering at 1260°C.⁴⁵ Adjustment of the temperature coefficient of resonant frequency was accomplished in the composite 0.96Li₃MgNbO₅-0.04CaTiO₃ sintered at 1250°C with $\epsilon_r = 19.12$, Qxf = 70 814 GHz (at 6.105 GHz), and $\tau_f = 2.6$ ppm/°C.⁴⁵

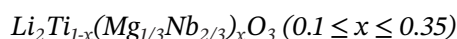


Li₃Mg₄NbO₈ with partial substitution of Zn²⁺ in the Mg²⁺ site was intended to reduce the dielectric loss and

contribute to the temperature stability. Specimens with $x = 0.02, 0.04, 0.06,$ and 0.08 in the Li₃(Mg_{1-x}Zn_x)₄NbO₈ were sintered in the 1050–1150°C range utilizing the stack-firing method (similar to the use of the powder bed procedure) to avoid Li loss. The bulk density and ϵ_r were higher for sintering at 1075°C and $x = 0.04$; the Qxf value reached 121 157 GHz and $\tau_f - 8.23$ ppm/°C.⁴⁶



The composites had their dielectric properties studied for $0.02 \leq x \leq 0.08$ after sintering in the 1200–1300°C range. The rock salt structure was identified in all compositions. The crystalline structure changed gradually from monoclinic to cubic as the fraction of Li₃Mg₂NbO₆ increased. The optimal dielectric properties were obtained for sintering at 1250°C and $x = 0.04$, with $\epsilon_r = 19.12$, Qxf = 70 814 GHz (at 6.105 GHz), and $\tau_f = 2.6$ ppm/°C.⁴⁷ In this particular case and other examples cited here, the production of a composite ceramic intended to adjust the temperature coefficient of the resonant frequency to near-zero values by the formation of a composite with opposite values of τ_f .



Partial substitution of (Mg_{1/3}Nb_{2/3})⁴⁺ for Ti⁴⁺ in the Li₂TiO₃ allowed adjusting τ_f to near-zero along with an increase in the Qxf value after sintering at 1170°C. The optimal dielectric properties were obtained for $x = 0.25$ in Li₂Ti_{1-x}(Mg_{1/3}Nb_{2/3})_xO₃ with $\epsilon_r \sim 19.6$, Qxf ~ 109 770 GHz, and $\tau_f \sim 1.2$ ppm/°C.⁴⁸ In a subsequent work,⁴⁹ the Li₂Ti_{0.75}(Mg_{1/3}Nb_{2/3})_{0.25}O₃ (LTMN_{0.25}) composition was mixed with 2 wt.% V₂O₅ or 1 wt.% 0.4 B₂O₃-0.6 CuO (BC) aiming to reduce the sintering temperature of LTMN_{0.25} to near 900°C. Specimens containing V₂O₅ were sintered in the 890–920°C range and co-fired with Al powder at 910°C, while the sintering temperatures of specimens with BC sintering aid were 860–890°C with co-firing at 870°C. Both sintering aids helped to decrease the sintering temperature below the melting point of silver (961°C) giving rise to dense microstructures, and with no diffusion of silver. The optimal dielectric properties ($\epsilon_r \sim 19.9$, Qxf ~ 60 950 GHz, and $\tau_f \sim -6.1$ ppm/°C) were obtained for 1 wt.% BC sintering at 870°C/2 h. A prototype dielectric resonator antenna fabricated with LTMN_{0.25}-0.6 CuO-0.4 B₂O₃ revealed good performance resonating at 10.02 GHz with a bandwidth ~ 175 MHz.⁴⁹



This ceramic, sintered at 1250°C/4 h, exhibited rock salt structure without secondary phases. Overfiring resulted in abnormal grain growth and porosity, due to Li loss. The optimal dielectric properties were: $\epsilon_r = 17.17$, Qxf = 51 519 GHz, and $\tau_f = -28.2$ ppm/°C.⁵⁰

$(1-x)[Li_2Ti_{0.98}Mg_{0.02}O_{2.96}F_{0.04}-1 \text{ wt. \% } Nb_2O_5] - x Li_3Mg_2NbO_6$ (LTMN_{0.02}-LMN), $0 \leq x \leq 0.1$)

The complex composition was sintered in the 1210–1250°C range. Single-phase with rock salt structure was obtained for all compositions. The addition of LMN was carried out to obtain a near-zero τ_f without loss of the other dielectric characteristics. A suitable sintering temperature of 1220°C resulted in high relative densities (~96%). Values of the dielectric properties were $\epsilon_r = 18.1$, Qxf = 105 661 GHz, and $\tau_f = 1.3 \text{ ppm/}^\circ\text{C}$ for $x = 0.08$.⁵¹

$Li_2Mg_3Ti_{1-x}(Zn_{1/3}Nb_{2/3})_xO_6$, ($0.02 \leq x \leq 0.08$)

Partial substitution of $(Zn_{1/3}Nb_{2/3})^{4+}$ in the Ti^{4+} site in $Li_2Mg_3TiO_6$ was also studied aiming to improve the Qxf value. The main goal was to produce a dielectric ceramic suitable for microstrip antenna application. Sintering experiments were carried out in the 1260–1360°C range. The bulk density increased with increasing x . The optimal properties were obtained for $x = 0.08$, sintered at 1285°C with $\epsilon_r = 13.28$, Qxf = 168 911 GHz, and $\tau_f = -42.88 \text{ ppm/}^\circ\text{C}$.⁵²

$Li_2Ti_{0.85}(Mg_{1/3}Nb_{2/3})_{0.15}O_3$

Attempts to stabilize the temperature coefficient of resonant frequency have been made by means of a tri-layer composition $Li_2Ti_{0.85}(Mg_{1/3}Nb_{2/3})_{0.15}O_3/MgTiO_3/Li_2Ti_{0.85}(Mg_{1/3}Nb_{2/3})_{0.15}O_3$ ceramic. The dielectric properties obtained were: $\epsilon_r = 18.4$, Qxf = 85 000 GHz, and $\tau_f = -3.8 \text{ ppm/}^\circ\text{C}$ (25–105°C), $\tau_f = 4.0 \text{ ppm/}^\circ\text{C}$ (–40 to 25°C).⁵³

$(1-m) Li_2TiO_3 - m Zn_3Nb_2O_8$ ($m = 0.1, 0.16, 0.2, 0.3$)

Ceramics sintered at 1100°C formed a solid solution with diffraction peaks characteristic of $Li_2ZnTi_3O_8$. The $Zn_3Nb_2O_8$ with negative τ_f , relatively high Qxf value, and low sintering temperature was selected to tune the τ_f value of Li_2TiO_3 . The average grain size increased from 10 to 23 μm when m increased from 0.1 to 0.3. For $m = 0.16$, optimum values of the dielectric properties were obtained with $\epsilon_r \sim 18.05$, Qxf = 25 791 GHz, and $\tau_f \sim -6.09 \text{ ppm/}^\circ\text{C}$.⁵⁴

$Li_4Mg_2NbO_6F$

LiF was added to lithium niobates to reduce the sintering temperature, due to its relatively low melting point (845°C). Moreover, the substitution of F^- into O^{2-} sites may reduce the oxygen bond strength. The specimens were sintered in the 850–950°C range. The relative density achieved high values ($\geq 97.5\%$) at 900°C. The optimal microwave dielectric properties were obtained after sintering at 900°C: $\epsilon_r \sim 15.53$, Qxf = 93 300 GHz, and $\tau_f \sim -39.8 \text{ ppm/}^\circ\text{C}$.⁵⁵

$Li_6MgTiNb_{1-x}V_xO_8F$ ($0 \leq x \leq 0.08$)

The $Li_6MgTiNbO_8F$ composition sintered at 1175°C with cubic rock salt structure exhibited Qxf = 105 700 ± 1600 GHz. It was found that Qxf values varied according to the density and the average grain size. The substitution of V^{5+} for Nb^{5+} decreased the sintering temperature while improving the relative density and relative permittivity. The $Li_6MgTiNb_{0.98}V_{0.02}O_8F$ composition sintered at 850°C/4 h showed $\epsilon_r = 18.14 \pm 0.05$, Qxf = 58 300 ± 1300 GHz, and $\tau_f = -42.66 \pm 0.33 \text{ ppm/}^\circ\text{C}$.⁵⁶

$Li_7(Nb_{1-x}Ti_x)_2O_{8-x}F$ ($0 \leq x \leq 0.10$)

Partial substitution in the Nb^{5+} site for Ti^{4+} was studied in a series of compounds sintered in the 675–950°C range. Sintering at 900°C yielded a minor fraction of Li_3NbO_4 secondary phase. Further increase of the sintering temperature increased the fraction of the secondary phase, which was attributed to lithium and fluorine volatilization; the Li_7NbO_8F composition sintered at 900°C showed $\epsilon_r = 16.98$, Qxf = 73 600 GHz, and $\tau_f = -41.6 \text{ ppm/}^\circ\text{C}$; $Li_7(Nb_{0.96}Ti_{0.04})_2O_{7.96}F$ ceramics sintered at 725°C/4 h showed a fine microstructure, well-suited with Ag powders, with $\epsilon_r = 17.54$, Qxf = 38 800 GHz, and $\tau_f = -44.8 \text{ ppm/}^\circ\text{C}$.⁵⁷

$(1-x) Li_{5.5}Nb_{1.5}O_6F - x Ba_3(VO_4)_2$

Composite ceramics with $x = 0, 0.15, 0.20, 0.25,$ and 0.30 were sintered in the 825–925°C range. Lithium niobate oxyfluoride, $Li_{5.5}Nb_{1.5}O_6F$, exhibited a single-phase rock salt structure. The τ_f value increased continuously with increasing barium vanadate content. The composite ceramic with $x = 0.25$ sintered at 825°C achieved $\epsilon_r = 16.68$, Qxf = 55 800 GHz, and $\tau_f = -1.7 \text{ ppm/}^\circ\text{C}$.⁵⁸

$Li_3Mg_4NbO_8$

The composition with orthorhombic structure was sintered in the 1075–1175°C range. This composition exhibited a partially ordered rock salt superstructure. Maximum density was achieved after sintering at 1150°C. The dielectric properties were: $\epsilon_r = 13.8$, Qxf = 103 400, and $\tau_f = -36 \text{ ppm/}^\circ\text{C}$.⁵⁹

2.2.5 | Compositions without lithium

In parallel with Li-based compositions, several ceramics without lithium were investigated. Extensive research work has been conducted on the dielectric properties of niobate-based ceramics.

$ZnZrNb_2O_8 + Li_2CO_3 - B_2O_3 - Bi_2O_3 - SiO_2$ (LBBS)

The LBBS, a boron-based glass sintering aid, was used with contents varying from 0.5 to 3.0 wt.% to sinter

pure-phase $\text{ZnZrNb}_2\text{O}_8$. The sintering aid allowed densification at relatively low temperatures. No secondary phases were detected by X-ray diffraction. In addition, LBBS significantly influenced the cell volume and NbO_6 octahedral distortion and, consequently, the dielectric properties. The compound with 0.75 wt.% LBBS sintered at 950°C had $\epsilon_r = 27.1$, $\text{Qxf} = 54\,500$ GHz, and $\tau_f = -48.7$ ppm/ $^\circ\text{C}$, besides chemical compatibility with silver electrodes.⁶⁰

$\text{ZnZrNb}_2\text{O}_8 + x \text{ wt.}\% \text{ LiF, MgF}_2, \text{ CuO} (0.00 \leq x \leq 0.10)$,
and $\text{Zn}_{1-x}\text{Cu}_x\text{ZrNb}_2\text{O}_8 (0.000 \leq x \leq 0.050)$

Small amounts of LiF, MgF_2 , and CuO were added as sintering aid. The additives significantly improved the dielectric properties of $\text{ZnZrNb}_2\text{O}_8$. Relevant properties were obtained for CuO additions: ϵ_r was found to depend on sample density. Doping with CuO promoted grain growth and decrease of the dielectric loss, with a consequent increase of the Qxf value. For $x = 0.06$, $\epsilon_r = 27.404$, $\text{Qxf} = 74\,213$ GHz, and $\tau_f = -52.779$ ppm/ $^\circ\text{C}$; for $x = 0.03$, $\epsilon_r = 27.448$, $\text{Qxf} = 72\,520$ GHz, and $\tau_f = -53.143$ ppm/ $^\circ\text{C}$.⁶¹

$(1-x)\text{ZnNb}_2\text{O}_6 - x\text{TiO}_2$

Different crystalline structures, including columbite, ixiolite, mixtures of ixiolite and rutile, and rutile, were obtained. The main goal was to tune ϵ_r and τ_f values with TiO_2 addition. The columbite structure can be interpreted as an ordered superstructure, and the introduction of TiO_2 into the crystalline structure resulted in a disordered system, with a consequent decrease of the Qxf value. The microwave dielectric properties were found to be primarily influenced by the crystalline phase rather than the chemical composition. The optimal properties were achieved for $x = 0.5$, where the structure was fully disordered, with $\epsilon_r = 34.3$, $\text{Qxf} = 42\,500$ GHz, and $\tau_f = -52$ ppm/ $^\circ\text{C}$.⁶²

$\text{Zn}_{1.01}\text{Nb}_2\text{O}_6/\text{TiO}_2/\text{Zn}_{1.01}\text{Nb}_2\text{O}_6$

The effects of the stacking scheme for sintering and of the TiO_2 content on the microwave dielectric properties of layered architectures were investigated. The reaction layer was found relatively thin (~ 12 μm). After sintering at 1200°C , τ_f was tuned to $\sim +0.53$ ppm/ $^\circ\text{C}$, with $\text{Qxf} \sim 99\,500$ GHz and $\epsilon_r \sim 26.8$.⁶³

$(1-x)\text{Zn}_{1.01}\text{Nb}_2\text{O}_6 - x\text{TiO}_2$

Among the dielectric ceramics with columbite structure, ZnNb_2O_6 is known to exhibit good microwave dielectric properties. Similar to Li-based dielectric ceramics, in this case, with an excess of only 0.01 mol of Zn, the Qxf value was improved from 121 000 to 138 000 GHz; for $x = 0.6$, the dielectric properties were: $\epsilon_r = 47.43$, $\text{Qxf} \geq 12\,300$ GHz, and $\tau_f = +13.9$ ppm/ $^\circ\text{C}$.⁶⁴

$\text{ZnTiNb}_2\text{O}_8 - x \text{ LBSCA} [x (\text{wt.}\%) = 0, 0.2, 0.4, 0.6, 0.8, 1]$

The LBSCA sintering aid was added to lower the sintering temperature of $\text{ZnTiNb}_2\text{O}_8$; a secondary phase (ZnNb_2O_6) was detected by X-ray diffraction; ceramics with $x = 0.4$ sintered at $950^\circ\text{C}/3$ h showed $\epsilon_r = 33.826$, $\text{Qxf} = 49\,143$ GHz, and $\tau_f = -57.59$ ppm/ $^\circ\text{C}$.⁶⁵

$\text{ZnTiNb}_2\text{O}_8$ (ZTN)

This dielectric ceramic was prepared from ZnNb_2O_6 and TiO_2 nanopowders prepared by high-energy ball milling. Pure ixiolite $\text{ZnTiNb}_2\text{O}_8$ ceramics with a relative density of up to 97% were obtained after sintering in the 975 – 1050°C range. The optimal dielectric properties were: $\epsilon_r = 35.5$, $\text{Qxf} = 52\,500$ GHz (at 6.7 GHz), and $\tau_f = -60.8$ ppm/ $^\circ\text{C}$.⁶⁶

$x\text{Zn}_{0.5}\text{Ti}_{0.5}\text{NbO}_4 - (1-x)\text{Zn}_{0.15}\text{Nb}_{0.3}\text{Ti}_{0.55}\text{O}_2, x = 0.0$ – 1.0

The structural evolution with x was thoroughly investigated, and a temperature-stable ceramic, that is, with a small variation of the dielectric properties with the temperature, was obtained for $x = 0.516$: $\epsilon_r \sim 46.11$, $\text{Qxf} \sim 27\,031$ GHz, and $\tau_f \sim -1.51$ ppm/ $^\circ\text{C}$.⁶⁷ The temperature coefficient of resonant frequency was tuned by combining a negative value of τ_f ($\text{Zn}_{0.5}\text{Ti}_{0.5}\text{NbO}_4$) with a positive value of τ_f ($\text{Zn}_{0.15}\text{Nb}_{0.3}\text{Ti}_{0.55}\text{O}_2$).

$(1-x)\text{ZnTiNb}_2\text{O}_8 - x\text{Zn}_{0.17}\text{Nb}_{0.33}\text{Ti}_{0.5}\text{O}_2 (0.35 \leq x \leq 0.75)$

The addition of $\text{Zn}_{0.17}\text{Nb}_{0.33}\text{Ti}_{0.5}\text{O}_2$ changed τ_f from -39.55 to 54.32 ppm/ $^\circ\text{C}$, increased ϵ_r from ~ 36.5 to ~ 51.9 , but the Qxf value decreased from 36 914 to 21 077 GHz as x increased. The sintered ceramics exhibited a bimodal distribution of grain sizes and the bulk density was higher for sintering at 1200°C . For $x = 0.55$, the ceramic sintered at $1200^\circ\text{C}/4$ h showed $\epsilon_r = 39.08$, $\text{Qxf} = 31\,384$ GHz, and $\tau_f = -6.45$ ppm/ $^\circ\text{C}$.⁶⁸

$\text{ZnTiNb}_2\text{O}_8 - x\text{CuTiNb}_2\text{O}_8 - 0.4 \text{ wt.}\% \text{ LBSCA} (0 \leq x \leq 0.4)$

To tune the temperature coefficient of resonant frequency, several compositions were prepared by the conventional solid-state synthesis method with polyvinyl alcohol as an organic binder. X-ray diffraction results reveal that increasing x , $\text{ZnTiNb}_2\text{O}_8$ transforms to ZnNb_2O_6 , and new phases ($\text{CuTiNb}_2\text{O}_8$ and Ti_3O_5) were formed at $x \geq 0.3$, influencing the microwave dielectric properties. Raman shift explained changes in the dielectric constant. For $x = 0.4$, high-density samples were obtained, but the Qxf value was comparatively low; this effect was attributed to grain boundaries and grain size. The following dielectric properties were obtained by sintering at 875°C with $x = 0.375$: $\epsilon_r = 35.01$, $\text{Qxf} = 19\,449$ GHz, and $\tau_f = -0.3$ ppm/ $^\circ\text{C}$; the highest Qxf value ($\sim 38\,711$ GHz) was obtained after sintering at 900°C with $x = 0.2$.⁶⁹

$Zn(Ta_{1-x}Nb_x)_2O_6$ ($0 \leq x \leq 0.3$)

Partial substitution of Ta in the Nb site was carried out aiming to obtain a high dielectric constant and near-zero temperature coefficient of the resonant frequency ceramic. The ceramics sintered at temperatures ranging from 1200 to 1300°C exhibited an increase in the dielectric constant and a decrease in the quality factor and temperature coefficient, as the value of x increased. The τ_f value decreased to near-zero with increasing x. At frequencies from 6 to 7 GHz and x = 0.3, the dielectric properties were: $\epsilon_r = 39.81$, Qxf = 42 800 GHz, and $\tau_f = 1.55$ ppm/°C.⁷⁰ The microwave dielectric properties of $Zn(Ta_{1-x}Nb_x)_2O_6$ were found to correlate with Ta/Nb-O bond ionicity.

 $Zn_{0.997}Cu_{0.003}ZrNb_2O_8 - TiO_2 + ZnO/TiO_2 + CuO/TiO_2 - Zn_{0.997}Cu_{0.003}ZrNb_2O_8$

The optimal dielectric properties were attributed to the stable three-layer structure design, and the doping with Cu^{2+} and Zn^{2+} to prevent the reduction of Ti^{4+} to Ti^{3+} . The three-layer ceramics sintered at 1240°C/6 h with 0.05 wt.% $TiO_2 + ZnO$ exhibited the dielectric characteristics: $\epsilon_r = 33.75$, Qxf = 59 000 GHz, and $\tau_f = +2.27$ ppm/°C.⁷¹

 $CaTi_{1-x}(Al_{0.5}Nb_{0.5})_xO_3$ ($0 \leq x \leq 0.75$)

The ceramics sintered at 1525–1550°C/3 h exhibited orthorhombic structure, bulk density values $\geq 98\%$, and the grain size ranging from ~ 9 to ~ 35 μm . The Qxf value first increased with x, due to the stable perovskite structure, with increased bond strength and covalence, but decreased at x = 0.75. In this case, similar to other reports, the secondary phase was explored to adjust the dielectric properties. An optimal combination of the dielectric properties was found for x = 0.45 with $\epsilon_r = 55.1$, Qxf = 49 700 GHz, and $\tau_f = 5$ ppm/°C.⁷²

 $(Zn_{1-x}Ni_x)ZrNbTaO_8$ ($0.02 \leq x \leq 0.10$)

Single-phase ceramics with wolframite structure were obtained after sintering in the 1130–1200°C range. The relative densities were higher than 95% and the grain size increased with Ni^{2+} addition. Solid solutions with monoclinic structure were found in the whole range of x. The optimal dielectric properties were obtained for x = 0.06 with $\epsilon_r = 27.88$, Qxf = 128 951 GHz, and $\tau_f = -39.9$ ppm/°C.⁷³

 $Ni_{0.4}Zn_{0.6}Ti_{(1-x)}Zr_xNb_2O_8$

The doping with Zr was intended to increase the quality factor and to obtain a thermally stable ceramic. The ixiolite structure disappeared when the Zr^{4+} content was higher than 0.2. The Qxf value was found to increase from 32 114 GHz (x = 0.1) to 45 733 GHz (x = 0.3), and the τ_f value changed from -38.1 ppm/°C (x = 0.3) to 3 ppm/°C (x = 0.1). $Ni_{0.4}Zn_{0.6}Ti_{0.7}Zr_{0.3}Nb_2O_8$, sintered at

1120°C/6 h, showed $\epsilon_r = 29.7$, Qxf = 92 078 GHz, and $\tau_f \sim -38$ ppm/°C.⁷⁴

 $(Ti_{0.6}Zr_{0.4})_{0.8}(Zn_{1/3}Nb_{2/3})_{0.2}O_2$

The dielectric properties of the $(Ti_{0.6}Zr_{0.4})_{0.8}(Zn_{1/3}Nb_{2/3})_{0.2}O_2$ ceramic were studied to determine the effects of the residual stress and dislocations on those parameters. The residual stress effect on microwave dielectric loss was reported using high-resolution Raman spectroscopy. It was found that the dielectric loss increases with increasing the residual stress. The ceramics with greater residual stress exhibited much higher dielectric loss, because it increased the vibration anharmonicity of the lattice. The composition sintered at 1200°C achieved $\epsilon_r = 41.1$, Qxf = 48 230 GHz (at 5.9 GHz), and $\tau_f = -9.7$ ppm/°C.⁷⁵

 $La(Nb_{1-x}Ta_x)O_4$ ($0 \leq x \leq 0.10$)

The ceramic compositions sintered at 1325°C exhibited a single monoclinic fergusonite structure. The evolution of the ϵ_r value was closely related to that of bond ionicity. The Qxf values showed similar behavior as the lattice energy and τ_f followed the bond energy variation. The optimal dielectric properties were obtained for x = 0.08 with relative density of 98%: $\epsilon_r = 19.23$, Qxf = 65 653 GHz, and $\tau_f = 3.03$ ppm/°C.⁷⁶

 $Ca_4La_2Ti_{5-x}(Mg_{1/3}Nb_{2/3})_xO_{17}$ ($0 \leq x \leq 4$)

Single-phase ceramics were obtained after sintering in the 1480–1560°C range. The ϵ_r of sintered ceramics decreased from 71.86 to 35.23, the Qxf value increased from 15 070 to 21 277 GHz, and τ_f varied from 125.2 to -16.7 ppm/°C, with x increasing from 0 to 4. A near-zero $\tau_f \sim -1.62$ ppm/°C was achieved at x = 3 with $\epsilon_r \sim 40.45$ and Qxf ~ 19 123 GHz.⁷⁷

 $LaTiNbO_6$

Sintering at 1300–1400°C yielded ceramics with monoclinic structure. However, annealing at 1100°C for 0.5–8 h promoted a gradual change to orthorhombic structure. The dielectric parameters were determined for several contents of monoclinic and orthorhombic phases. The values of ϵ_r and τ_f increased with increasing the amount of orthorhombic phase, whereas Qxf showed the opposite trend. For long annealing times, a pure orthorhombic phase was obtained with the following dielectric properties: $\epsilon_r = 48.7$, Qxf = 10 018 GHz, and $\tau_f = 69.7$ ppm/°C.⁷⁸

 $Mg_{0.5}Zn_{0.5}TiNb_2O_8$

To optimize the dielectric properties of $ZnTiNb_2O_8$, the partial substitution of Mg^{2+} at the Zn^{2+} site was investigated. The composition $Mg_{0.5}Zn_{0.5}TiNb_2O_8$ was sintered at temperatures ranging from 1100 to 1180°C. It was observed

that for sintering temperatures below 1120°C, the quality factor primarily depended on the density. However, for higher sintering temperatures, the quality factor was influenced by the crystal structure, and the temperature coefficient of the resonant frequency τ_f varied from approximately -3.2 to -5.3 ppm/°C as the bond strength of Mg/Zn-O decreased. Typical dielectric properties obtained after sintering at 1120°C were as follows: $\epsilon_r = 30.74$, Qxf = 66 900 GHz, and $\tau_f = -4.01$ ppm/°C.⁷⁹

MgZrNb₂O₈

A single-phase ceramic was obtained after sintering in the 1280–1360°C range; when sintered at $T_s < 1340^\circ\text{C}$, the Qxf value varied mainly according to the relative density; at $T_s > 1340^\circ\text{C}$, the quality factor depended also on the grain morphology. The specimen sintered at 1340°C/4 h, with an average grain size of ~ 2 μm , exhibited $\epsilon_r = 26$, Qxf = 120 816 GHz (at 6.85 GHz), and $\tau_f = -50.2$ ppm/°C.⁸⁰

MgZr_{0.85}Sn_{0.15}Nb₂O₈

The ceramics were sintered in the 1220–1340°C range to determine the effect of the sintering temperature on the dielectric properties of this composition. Characteristic wolframite structure was obtained with no trace of secondary phases. The maximum density value was obtained after sintering at 1260°C, the unit cell volume being the lowest. The ϵ_r value followed the same trend as the total bond ionicity, the Qxf values the total lattice energy, and the τ_f values the total bond energy. Typical microwave dielectric properties obtained at 1260°C were: $\epsilon_r = 24.91$, Qxf = 94 014 GHz, and $\tau_f = -43.93$ ppm/°C.⁸¹

Mg_{1-x}Ca_xZrNb₂O₈

A suitable Ca²⁺ concentration was able to increase Nb–O bond ionicity and Nb–O bond lattice energy, contributing to an improvement in the dielectric constant and Qxf value; the τ_f was influenced by the bond valence and thermal expansion coefficient of the Mg–O bond. The introduction of Ca²⁺ promoted changes in the microstructure of ceramics (grain shape and size). For $x = 0.04$, $\epsilon_r = 25.21$, Qxf = 116 000 GHz (at 7.17 GHz), and $\tau_f = -24.4$ ppm/°C.⁸²

MgZr_{1-x}Ti_xNb₂O₈ (0 ≤ x ≤ 0.4)

The ceramic compositions with organic binder (13 wt.% polyvinyl alcohol) were sintered in the 1240–1340°C range. The addition of Ti⁴⁺ promoted an increase of the bulk density. The introduction of Ti⁴⁺ in the crystal lattice reduced the volume of the unit cell and strengthened the bond covalence by changing the atomic distances in the ZrO₆ and NbO₆. The ϵ_r and Qxf values were considerably improved with Ti addition. Optimal dielectric

properties were obtained for $x = 0.1$ composition sintered at 1320°C: $\epsilon_r = 25.72$, Qxf = 130 123 GHz (at 7.308 GHz), and $\tau_f = -46.60$ ppm/°C.⁸³

(Mg_{1/3}Nb_{2/3})_x(Zr_{0.5}Ti_{0.5})_{1-x}O₂ (x = 0.00, 0.05, 0.10, 0.13, 0.15, and 0.20)

An appropriate amount of (Mg_{1/3}Nb_{2/3})⁴⁺ was found to increase the temperature stability and to reduce the microwave dielectric loss of ZrTiO₄. All specimens were single phase with orthorhombic structure, and relative densities higher than 96%. The average grain size increased from ~ 4 to ~ 8 μm with increasing (Mg_{1/3}Nb_{2/3}) content. The Qxf value increased with increasing the grain size; the ϵ_r and τ_f values decreased with increasing x . Both parameters were found dependent on the cation-cation distance, as well as on polarizability and relative density. The annealing approach was applied for reducing the intrinsic loss and improving the Qxf value. The optimum microwave dielectric properties were $\epsilon_r \sim 40.9$, Qxf ~ 40 217 GHz, and $\tau_f \sim 0.8$ ppm/°C, for $x = 0.13$.⁸⁴

MgNb₂O₆ doped with flake Al₂O₃ (0–5 wt.%)

The phase evolution, microstructure, microwave dielectric properties, and mechanical behavior were investigated. Flake Al₂O₃ was used as a second phase to promote good chemical stability and to improve the mechanical properties of MgNb₂O₆. The relative density decreased with increasing Al₂O₃ content. X-ray diffraction measurements revealed a secondary phase, characteristic of alumina, for additions higher than 1 wt.%. The ceramics doped with 1.0 wt.% Al₂O₃ exhibited $\epsilon_r = 20.1$, Qxf = 109 100 GHz, and $\tau_f = -69$ ppm/°C after sintering at 1300°C/4 h.⁸⁵

(Mg_{1/3}Nb_{2/3})_x(Zr_{0.4}Ti_{0.6})_{1-x}O₂ (x = 0.05–0.15)

Ceramics were obtained by two-step sintering (heating at 5°C/min to 1350°C/30 min and cooled down at 10°C/min to 1300°C/24 h) aiming to reduce the residual stress and improve the Qxf value; for $x = 0.12$, the microwave dielectric properties were $\epsilon_r \sim 40.7$, Qxf ~ 41 461 GHz (5 x that of the normal sintering ceramics), and $\tau_f \sim 1.23$ ppm/°C.⁸⁶

MgNb_{2-x}V_{x/2}O_{6-1.25x}

Low-temperature liquid phase sintering was achieved via the nonstoichiometric substitution of vanadium at the niobium site; for $x = 0.2$, the ceramic sintered at 1030°C/4 h achieved $\epsilon_r = 20.5$, Qxf = 91 000 GHz, and $\tau_f = -65$ ppm/°C.⁸⁷

Mg_{0.5}Zr_{0.5}NbO₄

Single monoclinic phase ceramics were obtained; the evolution of the dielectric properties with sintering temperature followed that of the density. The ϵ_r value was found to be related to Nb-O bond ionicity, and Qxf was

TABLE 1 Values of sintering temperature T_s (and time, when reported), dielectric constant ϵ_r , quality factor Qxf, and temperature coefficient τ_f of niobium-based compositions containing lithium.

Composition	Sintering T_s ($^{\circ}\text{C/h}$)	ϵ_r	Qxf (GHz)	τ_f (ppm/ $^{\circ}\text{C}$)	Ref.
Pure $\text{Li}_3\text{Mg}_2\text{NbO}_6$	1250	16.8	79 643	-27.2	35
	950	18	51 870	-23	22
$\text{Li}_3(\text{Mg}_{0.98}\text{Co}_{0.02})_2\text{NbO}_6$	1300/4	15.22	127600	-3.64	23
$\text{Li}_3(\text{Mg}_{0.96}\text{Ca}_{0.04})_2\text{NbO}_6 + 6 \text{ wt.}\% \text{ LiF}$	1140/6	16.81	122082	-25.8	24
	900/6	15.85	98012	-28.6	24
$\text{Li}_3\text{Mg}_{1.98}\text{Cu}_{0.02}\text{NbO}_6$	1100	15.75	92134	-2	10
$\text{Li}_3\text{Mg}_{1.9}\text{Sn}_{0.3}\text{Nb}_{0.8}\text{O}_6$ $\text{Li}_3\text{Mg}_{1.6}\text{Sn}_{1.2}\text{Nb}_{0.2}\text{O}_6$	1290/4	15.9	118700	-32.9	26
	1290/4	11.64	83100	3.9	26
$\text{Li}_3(\text{Mg}_{0.92}\text{Zn}_{0.08})_2\text{NbO}_6 + 0.5 \text{ wt}\% (0.17 \text{ Li}_2\text{O}-0.83\text{V}_2\text{O}_5)$	1120/4	17.2	142331	23.2	27
$\text{Li}_{3.04}\text{Mg}_{1.96}\text{Zn}_{0.04}\text{Nb}_{0.96}\text{Ti}_{0.04}\text{O}_6$	1120/4	14	83395	37.2	27
	925/2	16.3	93100	-34.1	28
$\text{Li}_3(\text{Mg}_{0.95}\text{A}_{0.05})_2\text{NbO}_6$ A= Ca^{2+}	1120-1240/4	15.62	96160	-18.47	25
A= Ni^{2+}		15.24	84810	-23.08	25
A= Zn^{2+}		15.39	82170	-18.57	25
A= Mn^{2+}		12.97	52700	-20.13	25
$\text{Li}_3\text{Mg}_2(\text{Nb}_{0.94}\text{Sb}_{0.06})\text{O}_6$	1150/6	15.79	94487	-24.53	29
$\text{Li}_3\text{Mg}_2\text{Nb}_{1.98}\text{V}_{0.02}\text{O}_6$	900/4	16	131000	-26	30
$\text{Li}_3\text{Mg}_2\text{VO}_6$	925	15.1	91000	-24	21
$\text{Li}_3\text{Mg}_2\text{Nb}_{0.98}\text{Ta}_{0.02}\text{O}_6$	1050-1150/4	15.58	113000	-4.5	11
$\text{Li}_3\text{Mg}_2(\text{Nb}_{0.94}\text{Mo}_{0.06})\text{O}_{6.03}$	1200/6	15.18	116266	-15.71	31
$\text{Li}_3\text{Mg}_2\text{Nb}_{0.94}\text{W}_{0.06}\text{O}_{6.03}$	1175/6	15.82	124187	18.28	32
$\text{Li}_{3.04}\text{Mg}_{1.92}\text{Nb}_{0.96}\text{Ti}_{0.08}\text{O}_6$	1050-1150/4	15.88	131000	-26.8	33
$\text{Li}_{3.02}\text{Mg}_{1.96}\text{Nb}_{0.98}\text{Ti}_{0.4}\text{O}_6$	1250/4	16.1	128600	-30.4	34
$\text{Li}_{3.9}\text{Mg}_{0.2}\text{Nb}_{0.1}\text{Ti}_{1.8}\text{O}_6$	1250/4	20.4	90300	2.9	34
$\text{Li}_3\text{Mg}_2\text{Nb}_{0.96}(\text{Li}_{1/5}\text{W}_{4/5})_{0.04}\text{O}_6$	1150/4	~14	114781	~22.3	35
$\text{Li}_3\text{Mg}_2\text{Nb}_{0.96}(\text{Mg}_{1/4}\text{W}_{3/4})_{0.04}\text{O}_6$		~13.8	105879	~21.2	35
$\text{Li}_3\text{Mg}_2\text{Nb}_{0.96}(\text{Al}_{1/3}\text{W}_{2/3})_{0.04}\text{O}_6$		~13.7	102760	~23.1	35
$\text{Li}_3\text{Mg}_2\text{Nb}_{0.96}(\text{Ti}_{1/2}\text{W}_{1/2})_{0.04}\text{O}_6$		~14.2	12838	~21.2	35
$\text{Li}_3\text{Mg}_2\text{Nb}_{0.96}\text{W}_{0.04}\text{O}_6$		16.8	79643	27.2	35
$\text{Li}_{3.06}\text{Mg}_2\text{Nb}_{0.94}\text{Ti}_{0.06}\text{O}_6$	1025/4	14.34	154113	-2.17	36
$\text{Li}_3\text{Mg}_2\text{NbO}_6 + 0.1 \text{ wt.}\% \text{ B}_2\text{O}_3$	925/4	14.0	67451	-16.82	37
$(\text{Li}_3\text{Mg}_2\text{NbO}_6-0.1 \text{ TiO}_2 + 1 \text{ wt.}\% \text{ LBBS}$ $(\text{Li}_2\text{O}-\text{B}_2\text{O}_3-\text{Bi}_2\text{O}_3-\text{SiO}_2)$	900/4	16	42648	-1	38
$\text{Li}_3\text{Mg}_2\text{NbO}_6 (0.5 \text{ wt.}\% \text{ MBS})$ MBS = $\text{MgO} + 45 \text{ B}_2\text{O}_3 + 13 \text{ SiO}_2$	925/4	14.5	80759	-20.7	39
0.5 wt.% ($52.45 \text{ Li}_2\text{O}:31.06 \text{ B}_2\text{O}_3:11.99 \text{ SiO}_2:2.25 \text{ CaO}:2.25$ Al_2O_3)	925/4	15.16	90557	-16.22	40
$\text{Li}_2\text{Ti}_{0.98}\text{Mg}_{0.02}\text{O}_{2.96}\text{F}_{0.04}-1 \text{ wt.}\% \text{ Nb}_2\text{O}_5 (\text{LTMN}) + \text{B}_2\text{O}_3-\text{CuO}$	790/4	24.44	60754	22.8	43
$0.85 \text{ Li}_3\text{NbO}_4-0.15 \text{ CaTiO}_3$	1025/4	21.9	24900	5.6	44
$\text{Li}_3\text{MgNbO}_5$	1260	16.2	96796	-24.8	45
$\text{Li}_3(\text{Mg}_{0.96}\text{Zn}_{0.04})_4\text{NbO}_8$	1075	15.0	121157	-8.23	46
$0.96 \text{ Li}_2\text{TiO}_3 - 0.04 \text{ Li}_3\text{Mg}_2\text{NbO}_6$	1250	19.12	70814	2.6	47
$\text{Li}_2\text{Ti}_{0.75}(\text{Mg}_{1/3}\text{Nb}_{2/3})_{0.25}\text{O}_3$	1150/2	19.6	109770	~1.2	48
$\text{Li}_2\text{Ti}_{0.75}(\text{Mg}_{1/3}\text{Nb}_{2/3})_{0.25}\text{O}_3 + 1.0\% (0.4 \text{ B}_2\text{O}_3-0.6 \text{ CuO})$	870/2	19.9	60950	-6.1	49

(Continues)

TABLE 1 (Continued)

Composition	Sintering T_s ($^{\circ}\text{C}/\text{h}$)	ϵ_r	Qxf (GHz)	τ_f (ppm/ $^{\circ}\text{C}$)	Ref.
$\text{Li}_5\text{ZnSnNbO}_8$	1250/4	17.17	51519	-28.2	50
0.92 [$\text{Li}_2\text{Ti}_{0.98}\text{Mg}_{0.02}\text{O}_{2.96}\text{F}_{0.04}$ -1 wt.% Nb_2O_5] - 0.08 $\text{Li}_3\text{Mg}_2\text{NbO}_6$ (LTMN _{0.02} -LMN)	1220	18.1	105661	1.3	51
$\text{Li}_2\text{Mg}_3\text{Ti}_{0.92}(\text{Zn}_{1/3}\text{Nb}_{2/3})_{0.08}\text{O}_6$	1285	13.28	168911	-42.88	52
$\text{Li}_2\text{Ti}_{0.85}(\text{Mg}_{1/3}\text{Nb}_{2/3})_{0.15}\text{O}_3$	1260/4	18.4	85000	3.8 (25–105 $^{\circ}\text{C}$), 4.0 (-40–25 $^{\circ}\text{C}$)	53
0.84 Li_2TiO_3 -0.16 $\text{Zn}_3\text{Nb}_2\text{O}_8$	1100	18.05	25791	-6.09	54
$\text{Li}_4\text{Mg}_2\text{NbO}_6\text{F}$	900	15.53	93300	-40	55
$\text{Li}_6\text{MgTiNb}_{0.98}\text{V}_{0.02}\text{O}_8\text{F}$	850/4	18.14	58300	-42.66	56
$\text{Li}_7\text{NbO}_8\text{F}$	900	16.98	73600	-41.6	57
$\text{Li}_7(\text{Nb}_{0.96}\text{Ti}_{0.04})_2\text{O}_{7.96}\text{F}$	725/4	17.54	38800	-44.8	57
(1-x) $\text{Li}_{3.5}\text{Nb}_{1.5}\text{O}_6\text{F}$ - x $\text{Ba}_3(\text{VO}_4)_2$	825	16.68	55800	-1.7	58
$\text{Li}_3\text{Mg}_4\text{NbO}_8$	1075–1175	13.8	103400	-36	59

dominated by the lattice energy and Nb-O bond energy. The ceramics sintered at 1350 $^{\circ}\text{C}/4$ h showed $\epsilon_r = 28.6$, Qxf = 82 000 GHz, and $\tau_f = -47$ ppm/ $^{\circ}\text{C}$.⁸⁸

$\text{MgTi}_{1-x}(\text{Zn}_{1/3}\text{Nb}_{2/3})_x\text{O}_3$ ($0 \leq x \leq 0.3$)

The quality factor was found to depend on the electronegativity difference and average covalence, the dielectric constant related to molecular polarizability and tolerance factor, and the temperature coefficient strongly correlated with TiO_6 octahedral distortion; the microwave dielectric properties of $\epsilon_r = 17.59$, Qxf = 211 600 GHz, and $\tau_f = -50$ ppm/ $^{\circ}\text{C}$ were obtained when $x = 0.12$, sintered at 1250 $^{\circ}\text{C}/4$ h.⁸⁹

$\text{Y}_{3-x}\text{Al}_5\text{Nb}_x\text{O}_{12+x}$ ($0 \leq x \leq 0.16$)

A single-phase solid solution of yttrium aluminum garnet structure was observed for $0 \leq x \leq 0.1$. A secondary phase, YNbO_4 , was detected for $x > 0.1$. It was found that the quality factor Qxf was a function of the grain size, and the temperature coefficient τ_f depended on the bond valence of the cations in the octahedra. The dielectric constant ϵ_r was influenced by density, ionic polarizability, and secondary phase. Doping $\text{Y}_3\text{Al}_5\text{O}_{12}$ with Nb and reducing the Y stoichiometry inhibited secondary phases. For $x = 0.1$, the composition sintered at 1700 $^{\circ}\text{C}/6$ h showed $\epsilon_r \sim 10.99$, Qxf ~ 280 387 GHz (at 13.5 GHz), and $\tau_f \sim -34.7$ ppm/ $^{\circ}\text{C}$.⁹⁰

Nb_2O_5 in $\text{Y}_3\text{Al}_5\text{O}_{12}$

Four compositions, $\text{Y}_3\text{Al}_5\text{O}_{12}$, $\text{Y}_3\text{Al}_5\text{O}_{12} + 1$ wt.% Nb_2O_5 , $\text{Y}_3\text{Al}_{4.955}\text{Nb}_{0.045}\text{O}_{12}$, and $\text{Y}_{2.955}\text{Al}_5\text{Nb}_{0.045}\text{O}_{12}$, were prepared to investigate the effects of Nb_2O_5 and non-stoichiometry on the dielectric properties of $\text{Y}_3\text{Al}_5\text{O}_{12}$. The ϵ_r value was found dependent on the sample den-

sity and polarizability; the Qxf value was improved with increasing the grain size, and the τ_f values were closely related to the bond valence of the cations in the AlO_6 octahedron. The optimal dielectric properties were found for Y-deficient composition ($\text{Y}_{2.955}\text{Al}_5\text{Nb}_{0.045}\text{O}_{12}$): $\epsilon_r \sim 10.37$, Qxf ~ 161 724 GHz, and $\tau_f \sim -33.8$ ppm/ $^{\circ}\text{C}$.⁹¹

$\text{BaZnP}_{2-x}\text{Nb}_x\text{O}_7$

A moderate amount of Nb^{5+} was found to promote the densification process. The results showed that ϵ_r was influenced by the density and the secondary phase ($\text{Ba}_3\text{Nb}_2\text{P}_4\text{O}_{18}$). The density and full width at half maximum of the Raman vibrational band played a critical role in affecting the Qxf values. Ceramics sintered at 925 $^{\circ}\text{C}$, with $x = 0.02$, exhibited $\epsilon_r = 7.98$, Qxf = 60 615 GHz ($\tan \delta = 2.18 \times 10^{-4}$; $f = 13.21$ GHz), and $\tau_f = -52.93$ ppm/ $^{\circ}\text{C}$.⁹²

$(\text{Na}_{0.5x}\text{La}_{1-0.5x})(\text{Nb}_{1-x}\text{Mo}_x)\text{O}_4$ ($0.0 \leq x \leq 1.0$)

Solid solutions with tetragonal scheelite structure were obtained for $0.4 \leq x < 1.0$. The quality factor Qxf was found to be influenced by grain size, porosity, and cleanliness of the grain boundaries. The τ_f value varied with x from ~ 27 to ~ -59 ppm/ $^{\circ}\text{C}$. Ceramics sintered at 1160 $^{\circ}\text{C}/2$ h and with $x = 0.5$ exhibited $\epsilon_r \sim 14.5$, Qxf ~ 45 600 GHz, and $\tau_f \sim -2.4$ ppm/ $^{\circ}\text{C}$.⁹³

$(\text{Sm}_{1-x}\text{Ca}_x)(\text{Nb}_{1-x}\text{Mo}_x)\text{O}_4$ ($x = 0.15-0.7$)

Simultaneous substitutions of the A and B cation in SmNbO_4 proved to be effective to optimize the dielectric properties. Specimens with $x < 0.375$ exhibited typical fergusonite-type structure, and the scheelite-type structure for $x \geq 0.375$. The dielectric constant was composition dependent; an optimum microwave dielectric

TABLE 2 Values of sintering temperature T_s (and time, when reported), dielectric constant ϵ_r , quality factor Qxf, and temperature coefficient τ_f of niobium-based compositions without lithium.

Composition	Sintering T_s ($^{\circ}$ C/h)	ϵ_r	Qxf (GHz)	τ_f (ppm/ $^{\circ}$ C)	Ref.
ZnZrNb ₂ O ₈ + 0.75 wt.% Li ₂ CO ₃ -B ₂ O ₃ -Bi ₂ O ₃ -SiO ₂ (LBBS)	950	27.1	54500	-48.7	60
ZnZrNb ₂ O ₈ + 0.06 wt.% LiF, MgF ₂ , CuO, and Zn _{0.94} Cu _{0.06} ZrNb ₂ O ₈	1200-1280/6	27.404	74213	-52.779	61
ZnZrNb ₂ O ₈ + 0.03 wt.% LiF, MgF ₂ , CuO and Zn _{0.97} Cu _{0.03} ZrNb ₂ O ₈		27.448	72520	-53.143	
0.5 ZnNb ₂ O ₆ - 0.5 TiO ₂	1250	34.3	42500	-52	62
Zn _{1.01} Nb ₂ O ₆ /TiO ₂ /Zn _{1.01} Nb ₂ O ₆	1200/4	26.8	99500	0.53	63
0.4 Zn _{1.01} Nb ₂ O ₆ - 0.6 TiO ₂	1100-1250/4	47.43	12300	13.9	64
ZnTiNb ₂ O ₈ - 0.4 wt.% LBSCA	950/3	33.826	49143	57.59	65
ZnTiNb ₂ O ₈ (ZTN)	975-1050	35.5	52500	-60.8	66
0.516 Zn _{0.5} Ti _{0.5} NbO ₄ - 0.484 Zn _{0.15} Nb _{0.3} Ti _{0.55} O ₂	1100/4	46.11	27031	-1.51	67
0.45 ZnTiNb ₂ O ₈ - 0.55 Zn _{0.17} Nb _{0.33} Ti _{0.5} O ₂	1200/4	39.08	31384	-6.45	68
ZnTiNb ₂ O ₈ - 0.375 CuTiNb ₂ O ₈ -0.4 wt.% LBSA	875	35.01	19449	-0.3	69
ZnTiNb ₂ O ₈ - 0.2 CuTiNb ₂ O ₈ -0.4 wt.% LBSA	900		38711		
Zn(Ta _{0.7} Nb _{0.3}) ₂ O ₆	1200-1300	39.81	42800	1.55	70
Zn _{0.997} Cu _{0.003} ZrNb ₂ O ₈ - TiO ₂ + ZnO/TiO ₂ + CuO/TiO ₂ - Zn _{0.997} Cu _{0.003} ZrNb ₂ O ₈	1240/6	33.75	59000	2.27	71
CaTi _{0.55} (Al _{0.5} Nb _{0.5}) _{0.45} O ₃	1525-1550	55.1	49700	5	72
(Zn _{0.94} Ni _{0.06})ZrNbTaO ₈	1130-1200	27.88	128951	39.9	73
Ni _{0.4} Zn _{0.6} Ti _{0.7} Zr _{0.3} Nb ₂ O ₈	1120/6	29.7	92078	~ -38	74
(Ti _{0.6} Zr _{0.4}) _{0.8} (Zn _{1/3} Nb _{2/3}) _{0.2} O ₂	1200	41.1	48230	-9.7	75
La(Nb _{0.92} Ta _{0.08})O ₄	1325	19.23	65653	3.03	76
Ca ₄ La ₂ Ti ₂ (Mg _{1/3} Nb _{2/3}) ₃ O ₁₇	1480-1560	40.45	19123	~1.62	77
LaTiNbO ₆	1300-1400	48.7	10018	69.7	78
Mg _{0.5} Zn _{0.5} TiNb ₂ O ₈	1120	30.974	66900	-4.1	79
MgZrNb ₂ O ₈	1340/4	26	120816	-50.2	80
MgZr _{0.85} Sn _{0.15} Nb ₂ O ₈	1260	24.91	94014	-43.93	81
Mg _{0.96} Ca _{0.04} ZrNb ₂ O ₈	1265-1375	25.21	116000	-24.4	82
MgZr _{0.9} Ti _{0.1} Nb ₂ O ₈	1320	25.72	130123	-46.60	83
(Mg _{1/3} Nb _{2/3}) _{0.13} (Zr _{0.5} Ti _{0.5}) _{0.87} O ₂	1375/4	~40.9	~40217	~0.8	84
MgNb ₂ O ₆ doped Al ₂ O ₃ (1 wt.%)	1300/4	20.1	109100	-69	85
(Mg _{1/3} Nb _{2/3}) _{0.12} (Zr _{0.4} Ti _{0.6}) _{0.88} O ₂	1350/0.5	~40.7	~41461	~1.23	86
MgNb _{1.8} V _{0.1} O _{3.5}	1030/4	20.5	91000	-65	87
Mg _{0.5} Zr _{0.5} NbO ₄	1350/4	28.6	82000	-47	88
MgTi _{0.88} (Zn _{1/3} Nb _{2/3}) _{0.12} O ₃	1250/4	17.59	211600	-50	89
Y _{2.9} Al ₅ Nb _{0.1} O _{12.1}	1700/6	10.99	280387	-34.7	90
Y _{2.955} Al ₅ Nb _{0.045} O ₁₂	1670-1750	10.37	161724	-33.8	91
BaZnP _{1.98} Nb _{0.02} O ₇	925	7.98	60615	-52.93	92
(Na _{0.25} La _{0.75})(Nb _{0.5} Mo _{0.5})O ₄	1160/2	~14.5	~45600	~-2.4	93
(Sm _{0.82} Ca _{0.18})(Nb _{0.82} Mo _{0.18})O ₄	1460-1540/3	17.1	52800	-1.4	94
Ba ₃ Ti _{3.4} (Co _{1/3} Nb _{2/3}) _{0.6} Nb ₄ O ₂₁	950	~40.99	~17310	~-8.62	95

performance for ceramics sintered at 1460–1540°C/3 h was achieved for $x = 0.18$, with $\epsilon_r \sim 17.1$, $Q_{xf} \sim 52\,800$ GHz (at ~ 8.80 GHz), and $\tau_f \sim -1.4$ ppm/°C.⁹⁴

$Ba_3Ti_{4-x}(Co_{1/3}Nb_{2/3})_xNb_4O_{21}$ ($0 \leq x \leq 12$)

Addition of $(Co_{1/3}Nb_{2/3})^{4+}$ in the Ti site and LBSCA glass along with organic binder as sintering aid were found effective to enhance the dielectric properties of the base ceramic sintered in the 925–975°C. All sintered specimens showed hexagonal lattice along with high density. The optimal dielectric properties were obtained for 0.6 wt.% LBSCA and sintering at 950°C: $\epsilon_r \sim 40.99$, $Q_{xf} \sim 17\,310$ GHz, and $\tau_f \sim -8.62$ ppm/°C.⁹⁵

3 | REMARKS

Most of the experiments here reported were performed looking for lowering the sintering temperature, increasing the dielectric constant and the quality factor, and reducing the temperature dependence of the dielectric ceramics. However, accomplishing these objectives is challenging, although a great deal of strong candidates already exists, as summarized in Tables 1 and 2.

As shown in the previous section, among the niobium-based compositions, those containing lithium occupy a prominent position. Another issue worth mentioning is the method of obtaining ceramics using organic binders and sintering aids. Regarding the sintering step, one of the main concerns has been the minimization of component losses. Several works report the addition of a compound, with structural characteristics similar to that of the base composition, but able to exert a compensation effect to obtain a near-zero temperature coefficient. These and other approaches used during the processing of ceramics proved to be effective for the optimization of the dielectric ceramics. Nevertheless, the application of these dielectric materials has been limited due to their relatively low-quality factor (Q_{xf}) values or inadequate thermal stabilities.

Tables 1 and 2 show values of the dielectric constant, the quality factor, and the temperature coefficient of the ceramic compositions reported in this review.

After analyzing the data presented in Tables 1 and 2, Figures 2 and 3 were created to visually illustrate the relationships between different parameters. The observations from Figures 2 and 3 are as follows: (1) there is an inverse correlation between the quality factor and the dielectric constant. Higher quality factors correspond to lower dielectric constants; (2) the temperature coefficient remains within the range of approximately -45 to $+38$ ppm/°C for dielectric constants ranging from 12 to 25; and (3) the quality factor falls within the range of

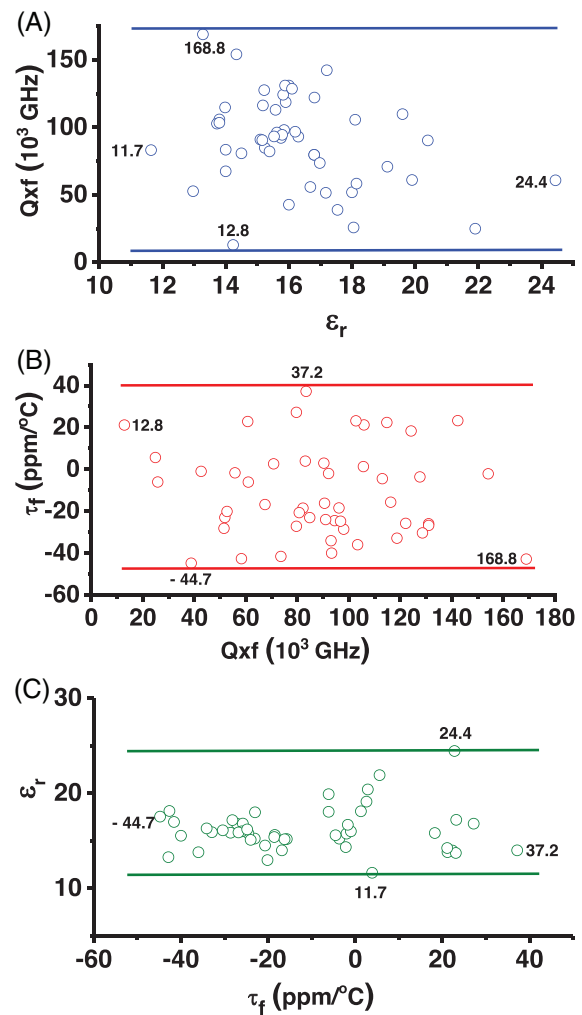


FIGURE 2 Plots of relationships between quality factor, dielectric constant, and temperature factor, after data measured in several lithium magnesium niobate ceramic compounds, collected from Table 1; the lines are guide to the eyes.

approximately 12 000–170 000 GHz. From these figures, it is evident that there is considerable variation in these parameters among different compositions. Therefore, the selection of compositions based on oxides for telecommunication devices by industries depends on various factors, such as the sustainability of material production, material availability and cost, fabrication cost, reproducibility tests and, of course, dielectric properties suitable for telecommunication applications. The presented data and observations may serve as a valuable reference for industries and researchers in making informed decisions regarding the selection and optimization of ceramic compositions for use in telecommunication devices.

Ceramics incorporating niobium in their composition have been successfully developed showing promising dielectric properties, making them suitable candidates for integration into 5G telecommunication devices. Researchers from around the world are actively engaged

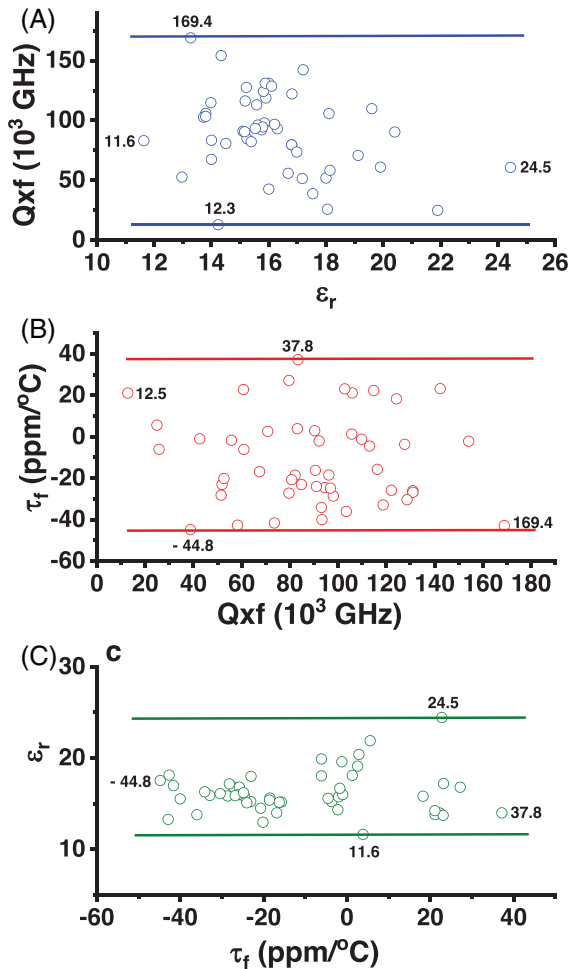


FIGURE 3 Plots of relationships between quality factor, dielectric constant, and temperature factor, after data measured in several lithium magnesium niobate ceramic compounds, collected from Table 2; the lines are guide to the eyes.

in conferences and publishing reports on these ceramics in indexed journals. These publications primarily focus on identifying compositions that exhibit the desired dielectric properties and investigating the relationship between these properties and microstructural features. In addition to the proposed tantalate, titanate, and silicate compositions, this review presents data on more than 80 different niobium-containing compositions, specifically niobates. The main emphasis is on collecting and analyzing data related to the dielectric constant, quality factor, and temperature coefficient, as these parameters play a crucial role in the design and performance of electronic devices for telecommunication applications. The ongoing research and publication of findings in this field highlight the growing interest and efforts to develop advanced niobium-containing ceramics with optimized dielectric properties for the evolving needs of 5G telecommunication systems.

Although the basic properties of the ceramic compositions containing niobium have been investigated, several studies are still needed to demonstrate their reliability for commercialization, such as integration in devices and tests under extreme conditions. The provided data in this paper, in an organized manner, shall serve to feed machine learning efforts for the development of a new generation of Nb-based dielectrics.

AUTHOR CONTRIBUTIONS

Statement of contribution for each author: R. Muccillo (design, collecting references, writing, approval); E.N.S. Muccillo (collecting references, writing).

CONFLICT OF INTEREST STATEMENT

The authors state that there is no conflict of interest.

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